SHANGHAI SUNRISE ELECTRONICS CO., LTD.

RS1AB THRU RS1MB SURFACE MOUNT FAST SWITCHING RECTIFIER

TECHNICAL SPECIFICATION

VOLTAGE: 50 TO 1000V CURRENT: 1.0A

FEATURES

- Ideal for surface mount pick and place application
- Low profile package
- Built-in strain relief
- High surge capability
- Glass passivated chip
- Fast recovery for high efficiency
- High temperature soldering guaranteed: 260°C/10sec/at terminal

MECHANICAL DATA

- Terminal: Plated leads solderable per MIL-STD 202E, method 208C
- Case: Molded with UL-94 Class V-O
 - recognized flame retardant epoxy
- Polarity: Color band denotes cathode

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Single-phase, half-wave, 60Hz, resistive or inductive load rating at 25°C, unless otherwise stated, for capacitive load, derate current by 20%)

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RATINGS	SYMBOL	RS1 AB	RS1 BB	RS1 DB	RS1 GB	RS1 JB	RS1 KB	RS1 MB	UNITS
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current (T _L =110°C)	I _{F(AV)}	1.0						А	
Peak Forward Surge Current (8.3ms single half sine-wave superimposed on rated load)	I _{FSM}	30						А	
Maximum Instantaneous Forward Voltage (at rated forward current)	V _F				1.3				V
Maximum DC Reverse Current $T_a=25^{\circ}C$ (at rated DC blocking voltage) $T_a=125^{\circ}C$		5.0 200							μΑ μΑ
Maximum Reverse Recovery Time (Note 1)) trr	150 250 500				00	nS		
Typical Junction Capacitance (Note 2)) C _J	15							pF
Typical Thermal Resistance (Note 3)) R _θ (ja)	30							°C/W
Storage and Operation Junction Temperature Note:	T_{STG},T_{J}	-50 to +150						°C	

1. Reverse recovery condition I_F =0.5A, I_R =1.0A, Irr=0.25A.

2.Measured at 1.0 MHz and applied voltage of $4.0V_{\rm dc}$

3. Thermal resistance from junction to terminal mounted on 5×5mm copper pad area